Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attomey's Docket N . 06816/017003	Application No.	
•	losure Statement	Applicant Eric R. Fossum, et al.		
(Use several sheets if n cessary) (37 CFR §1.98(b))		Filing Date June 27, 2000	Group Art Unit	

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(Us severa	I sheets if necessary)	Filing Date June 27, 2000	Group Art Unit	

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	AMMM	Hynecek, "BCMD - An Improved Photosite Structure for High-Density Image Sensors," IEEE Transactions on Electron Devices, Vol., 38(5), pp. 1011-1020 (May 1991)
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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office		Application No.
Informati n Disclosure Statement by Applicant (Us several sheets if necessary) (37 CFR §1.98(b))		Applicant Eric R. Fossum, et al.	
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PD	AA	5,345,266	Sep. 6, 1994	Denyer			
	AB	5,153,421	Oct. 6, 1992	Tandon et al.			
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	AD	5,198,654	Mar. 30, 1993	Mukainakano et al.			<u></u>
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		AB	4	1	5	5	0	9	4	5/1979	Ohba; et al.		257	292		
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EXAMINER

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. Application No. 06816-017005				
	closure Statement oplicant	Applicant Eric R. Fossum et al.				
	eets if necessary)	Filing Date	Group Art Unit			
(37 CFR §1.98(b))		•				

U.S. Patent Documents								
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate	
P	AA	4,407,010	09/1983	Baji et al.				
1	AB	5,345,266	09/1994	Denyer				
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Foreign Patent Documents or Published Foreign Patent Applications								
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	AL							
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	Other Documents (include Author, Title, Date, and Place of Publication)								
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